

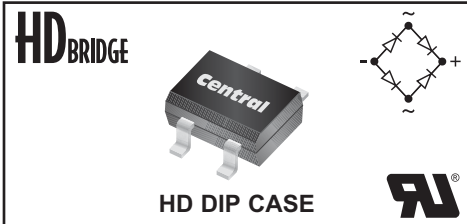
CBRHD-01
SURFACE MOUNT
HIGH DENSITY
0.8 AMP
SILICON BRIDGE RECTIFIER



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CBRHD-01 is a silicon full wave bridge rectifier mounted in a durable epoxy surface mount molded case, utilizing glass passivated chips.



MARKING CODE: CBD1

FEATURES:

- Efficient use of board space: requires only 42mm² of board space vs. 120mm² of board space needed for industry standard 1.0 Amp surface mount bridge rectifier.
- 50% higher density (Amps/mm²) than the industry standard 1.0 Amp surface mount bridge rectifier.
- Glass passivated chips for high reliability.

• This series is UL listed: file number E130224

MAXIMUM RATINGS: (T_A=25°C unless otherwise noted)

	SYMBOL		UNITS
Peak Repetitive Reverse Voltage	V _{RRM}	100	V
DC Blocking Voltage	V _R	100	V
RMS Reverse Voltage	V _{R(RMS)}	70	V
Average Forward Current (T _A =40°C) (Note1)	I _O	0.5	A
Average Forward Current (T _A =40°C) (Note 2)	I _O	0.8	A
Peak Forward Surge Current	I _{FSM}	30	A
Operating and Storage Junction Temperature	T _J , T _{stg}	-65 to +150	°C
Thermal Resistance (Note 3)	θ _{JA}	85	°C/W

ELECTRICAL CHARACTERISTICS PER DIODE: (T_A=25°C unless otherwise noted)

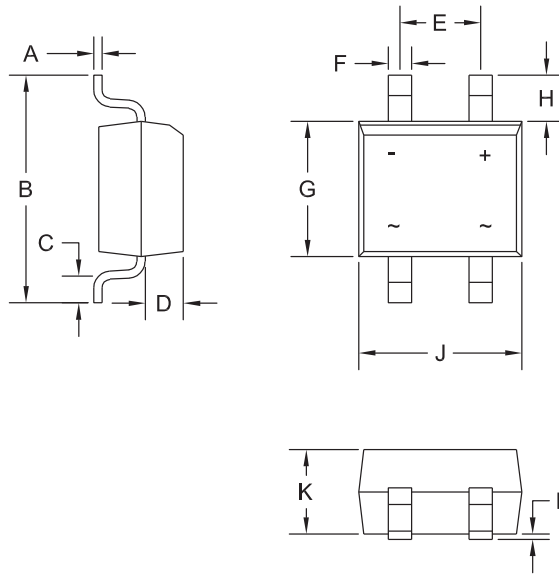
SYMBOL	TEST CONDITIONS	TYP	MAX	UNITS
I _R	V _R = 100V		5.0	μA
I _R	V _R = 100V, T _A =125°C		500	μA
V _F	I _F =400mA		1.0	V
C _J	V _R =4.0V, f=1.0MHz	9.0		pF

- Notes: (1) Mounted on Glass-Epoxy PCB.
(2) Mounted on Ceramic PCB.
(3) Mounted on PCB with 0.5" x 0.5" copper pads.

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HD DIP CASE - MECHANICAL OUTLINE



R2

DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.006	0.014	0.15	0.35
B	-	0.275	-	7.00
C	0.027	0.043	0.70	1.10
D	0.035	0.051	0.90	1.30
E	0.090	0.106	2.30	2.70
F	0.019	0.031	0.50	0.80
G	0.150	0.165	3.80	4.20
H	0.051	0.067	1.30	1.70
J	0.177	0.193	4.50	4.90
K	0.090	0.106	2.30	2.70
L	0.000	0.008	0.00	0.20

HD DIP (REV: R2)

MARKING CODE: CBD1

R2 (4-January 2010)